

TSM4936D 30V N-Channel MOSFET



SOP-8

Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
30	36 @ V _{GS} = 10V	5.9
	53 @ V _{GS} = 4.5V	4.9

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

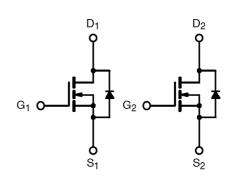
- High-Side DC/DC Conversion
- Notebook
- Sever

Ordering Information

Part No.	Package	Packing
TSM4936DCS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	5.9	А	
Pulsed Drain Current		I _{DM}	40	А	
Continuous Source Current (Diode Conduction) ^{a,b}		Is	1.0	А	
Maximum Power Dissipation	Ta = 25°C	D	3.0	W	
	Ta = 75°C	P _D	2.1		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	32	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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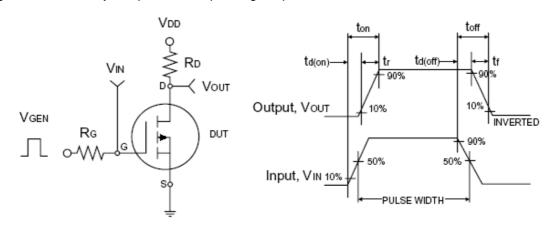


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	30			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1	1.4	3	V	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}			1.0	μΑ	
On-State Drain Current ^a	$V_{DS} \ge 5V$, $V_{GS} = 10V$	I _{D(ON)}	30			Α	
Dunin Course On Chata Basistanas	$V_{GS} = 10V, I_D = 5.9A$	_		32	36	mΩ	
Drain-Source On-State Resistance ^a	$V_{GS} = 4.5V, I_D = 4.9A$	R _{DS(ON)}		42	53		
Forward Transconductance ^a	$V_{DS} = 15V, I_{D} = 5.9A$	g _{fs}		15		S	
Diode Forward Voltage	$I_S = 1A$, $V_{GS} = 0V$	V_{SD}		0.76	1.0	V	
Dynamic ^b					_		
Total Gate Charge	$V_{DS} = 15V, I_D = 5.9A,$	Q_g		13			
Gate-Source Charge	$V_{DS} = 15V, I_D = 5.9A,$ $V_{GS} = 10V$	Q_gs		4.2		nC	
Gate-Drain Charge	V _{GS} = 10V	Q_gd		3.1			
Input Capacitance	\/ 45\/ \/ 0\/	C _{iss}		610			
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		100		pF	
Reverse Transfer Capacitance	I = I.UIVIMZ	C_{rss}		77			
Switching ^c							
Turn-On Delay Time	\\ 45\\ D 450	t _{d(on)}		9.1			
Turn-On Rise Time	$V_{DD} = 15V, R_L = 15\Omega,$	t _r		16.5		~ C	
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$	t _{d(off)}		23		nS	
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		3.5			

Notes:

- a. pulse test: PW \leq 300µS, duty cycle \leq 2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

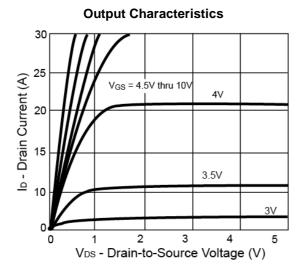
Switchin Waveforms



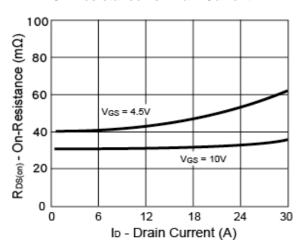
30V N-Channel MOSFET



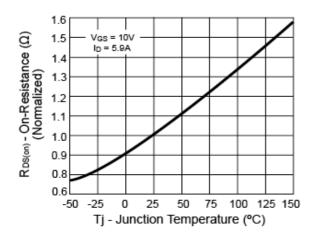
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



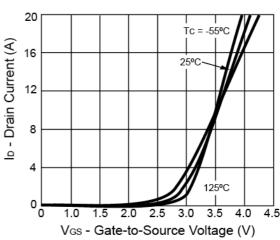
On-Resistance vs. Drain Current



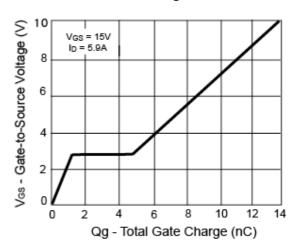
On-Resistance vs. Junction Temperature



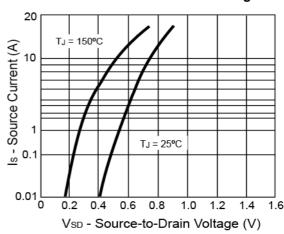
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



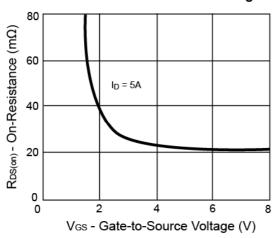


30V N-Channel MOSFET



Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage



0.2 0.1 ID = 1mA -0.0 -0.1 -0.2

25

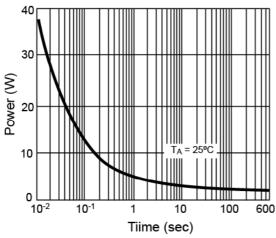
75

50 Tj - Junction Temperature (°C)

100 125 150

Threshold Voltage

Single Pulse Power



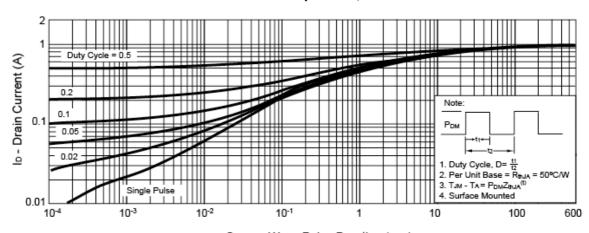
Normalized Thermal Transient Impedance, Junction-to-Ambient

V_{GS(th)} - Variance (V)

-0.3

-0.4

. -50 -25



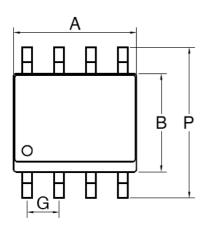
Square Wave Pulse Duration (sec)



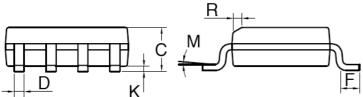
30V N-Channel MOSFET



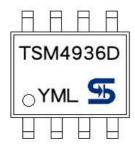
SOP-8 Mechanical Drawing



SOP-8 DIMENSION DIM MILLIMETERS INCHES MIN MAX MIN MAX. A 4.80 5.00 0.189 0.196 B 3.80 4.00 0.150 0.157 C 1.35 1.75 0.054 0.068 D 0.35 0.49 0.014 0.019 F 0.40 1.25 0.016 0.049 G 1.27BSC 0.05BSC K 0.10 0.25 0.004 0.009 M 0° 7° 0° 7° P 5.80 6.20 0.229 0.244 R 0.25 0.50 0.010 0.019						
DIM MIN MAX MIN MAX. A 4.80 5.00 0.189 0.196 B 3.80 4.00 0.150 0.157 C 1.35 1.75 0.054 0.068 D 0.35 0.49 0.014 0.019 F 0.40 1.25 0.016 0.049 G 1.27BSC 0.05BSC K 0.10 0.25 0.004 0.009 M 0° 7° 0° 7° P 5.80 6.20 0.229 0.244	SOP-8 DIMENSION					
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M 0° 7° 0° 7° P 5.80 6.20 0.229 0.244	G	1.27BSC		0.05	BSC	
P 5.80 6.20 0.229 0.244	K	0.10	0.25	0.004	0.009	
	M	00	7°	00	7°	
R 0.25 0.50 0.010 0.019	Р	5.80	6.20	0.229	0.244	
	R	0.25	0.50	0.010	0.019	



Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

5

L = Lot Code



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